

150V(D-S) N-Channel Enhancement Mode Power MOS FET

General Features

- $V_{DS}=150V, I_D=100A$
 $R_{DS(ON)} < 12m\Omega @ V_{GS}=10V$ (Typ:9.8m Ω)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability



Lead Free

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

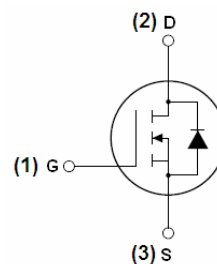
PIN Configuration



Marking and pin assignment



TO-220-3L top view



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MSN15B0K	MSN15B0K	TO-220-3L	-	-	-

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	100	A
Drain Current-Continuous($T_C=100^{\circ}C$)	$I_D(100^{\circ}C)$	70	A
Pulsed Drain Current	I_{DM}	390	A
Maximum Power Dissipation	P_D	370	W
Derating factor		2.47	W/ $^{\circ}C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	1100	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Cas ^e (Note 2)	$R_{\theta JC}$	0.41	°C/W
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

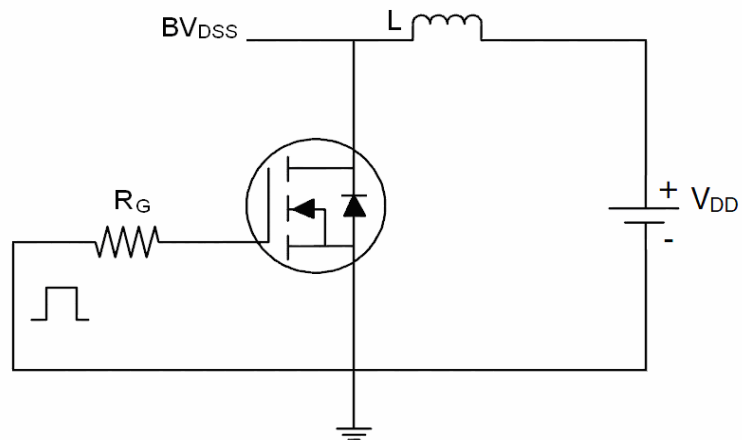
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	170	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3.2	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	9.8	12	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =40A	150	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, F=1.0MHz	-	13000	-	PF
Output Capacitance	C _{OSS}		-	640	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	556	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =2A, R _L =15Ω , R _G =2.5Ω, V _{GS} =10V	-	32.5	-	nS
Turn-on Rise Time	t _r		-	30	-	nS
Turn-Off Delay Time	t _{d(off)}		-	113	-	nS
Turn-Off Fall Time	t _f		-	48	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =30A, V _{GS} =10V	-	326	-	nC
Gate-Source Charge	Q _{gs}		-	62	-	nC
Gate-Drain Charge	Q _{gd}		-	128	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =40A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	100	A
Reverse Recovery Time	t _{rr}	T _j =25℃, I _F =75A, di/dt=100A/μs (Note3)	-		52.5	nS
Reverse Recovery Charge	Q _{rr}		-		82.5	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

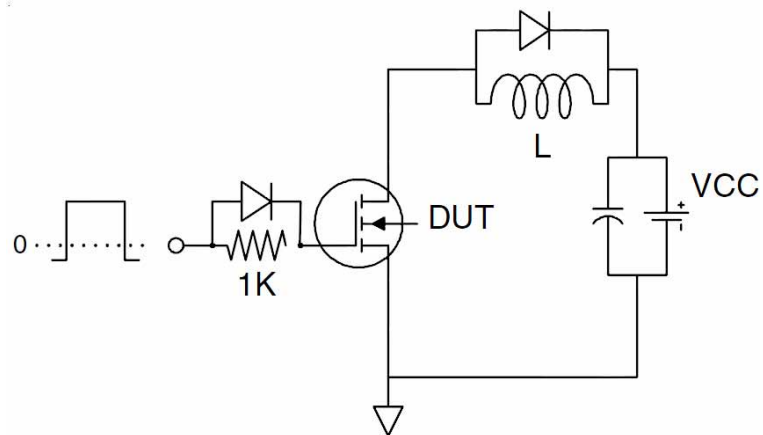
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DS}=40V, V_G=10V, L=0.5mH, R_g=25\Omega$

Test circuit

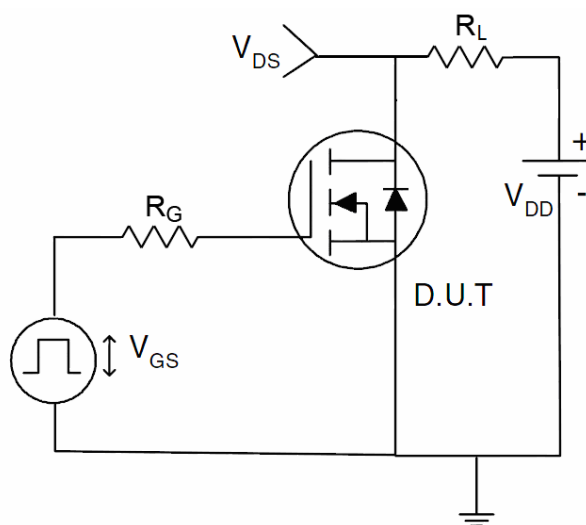
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

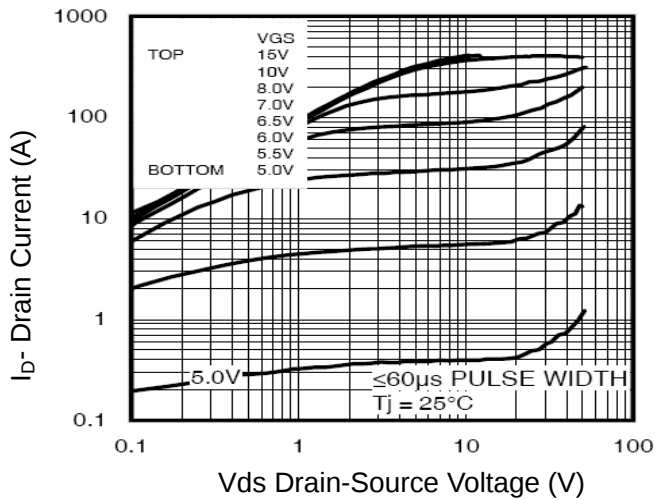


Figure 1 Output Characteristics

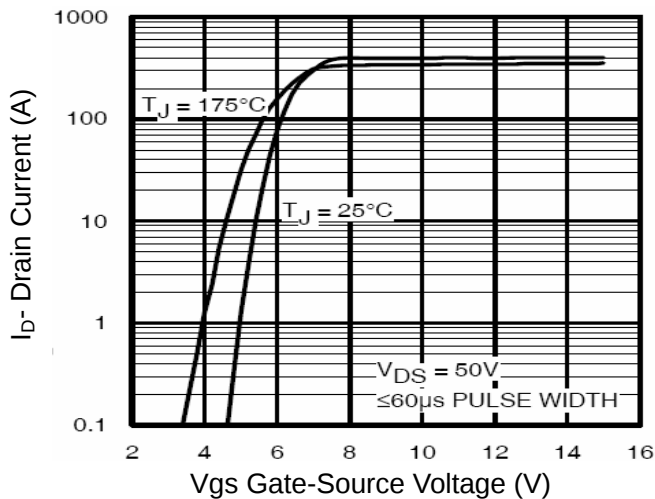


Figure 2 Transfer Characteristics

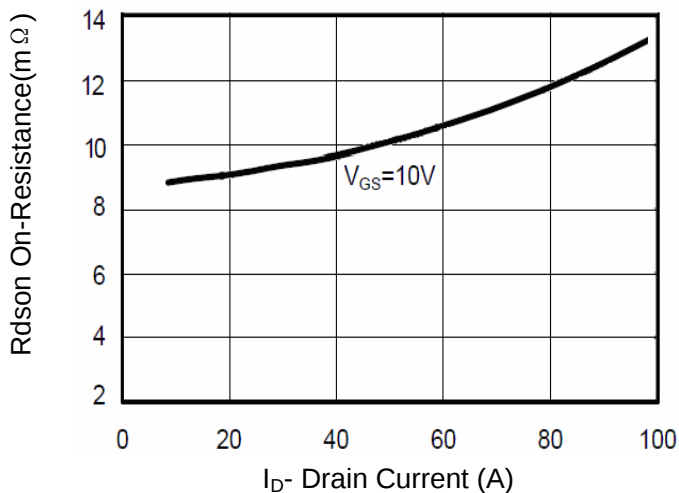


Figure 3 $R_{DS(on)}$ - Drain Current

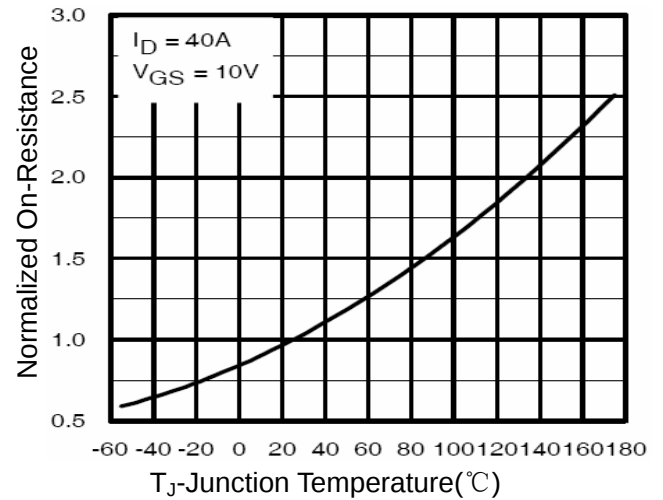


Figure 4 $R_{DS(on)}$ -Junction Temperature

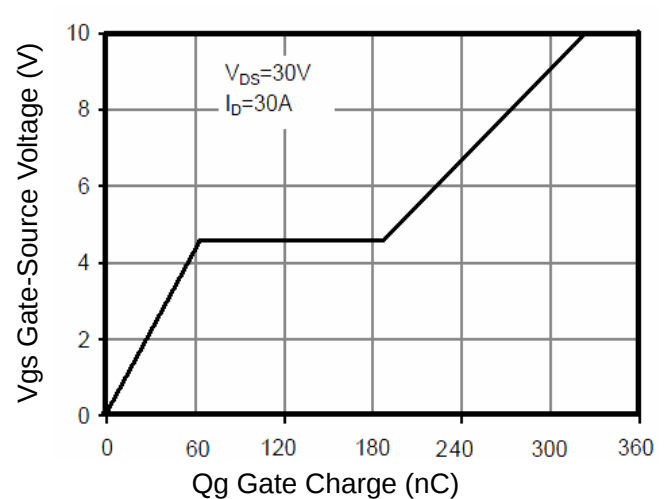


Figure 5 Gate Charge

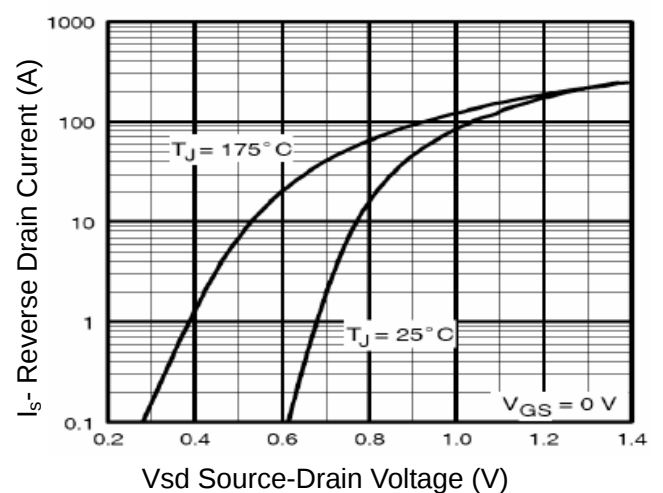


Figure 6 Source- Drain Diode Forward

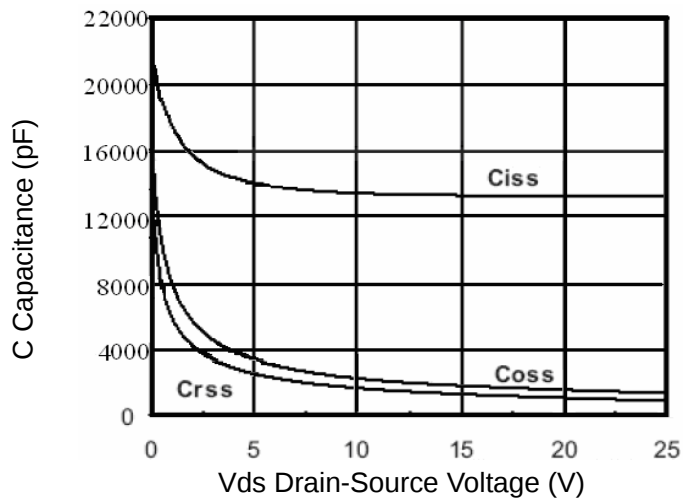


Figure 7 Capacitance vs V_{DS}

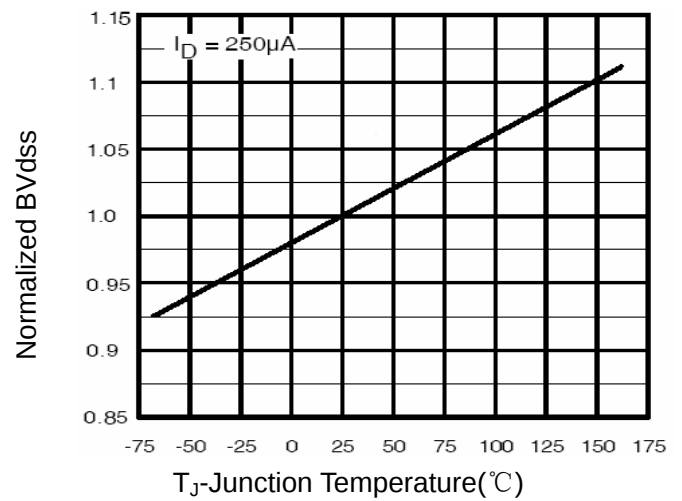


Figure 9 BV_{DSS} vs Junction Temperature

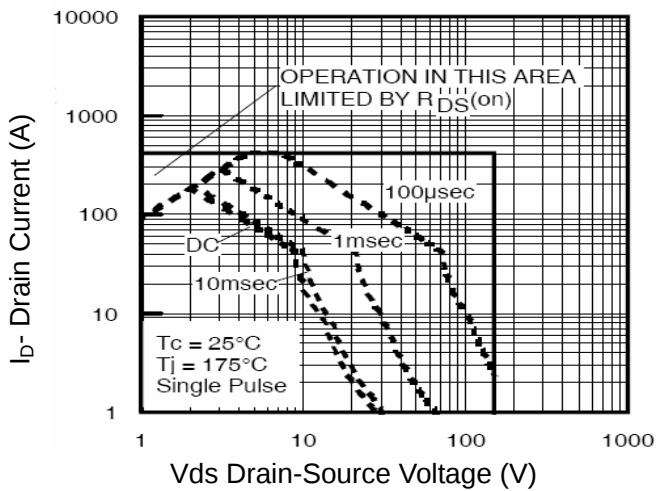


Figure 8 Safe Operation Area

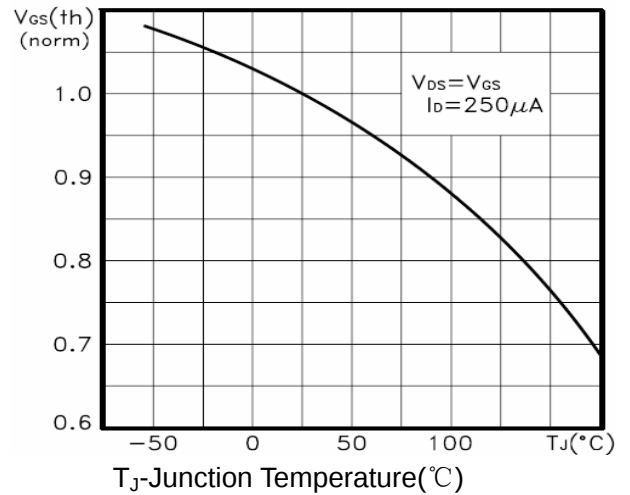


Figure 10 $V_{GS(th)}$ vs Junction Temperature

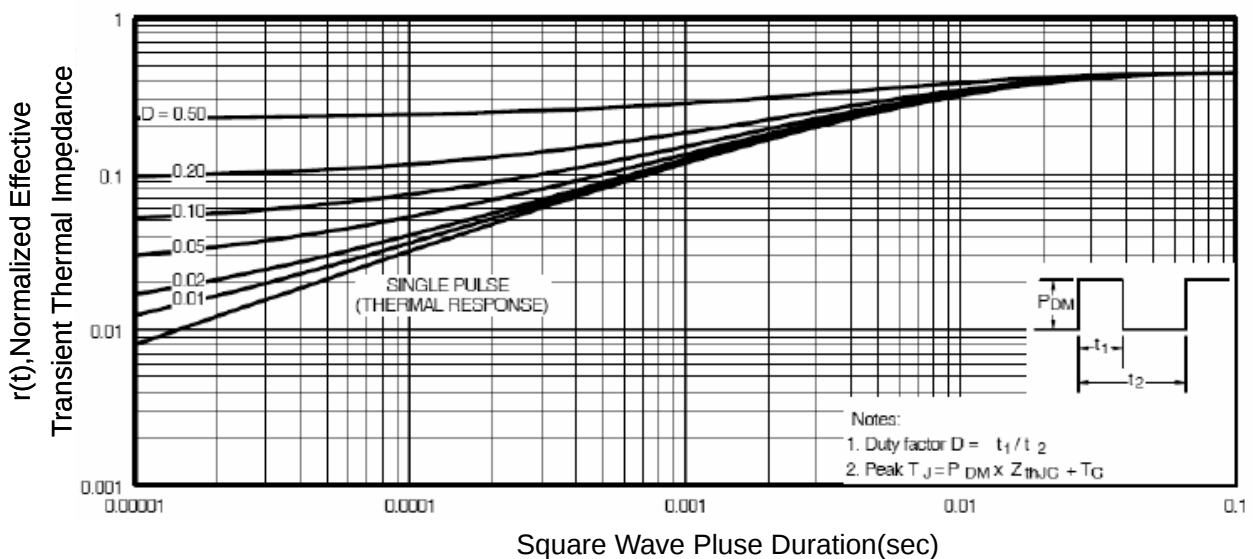
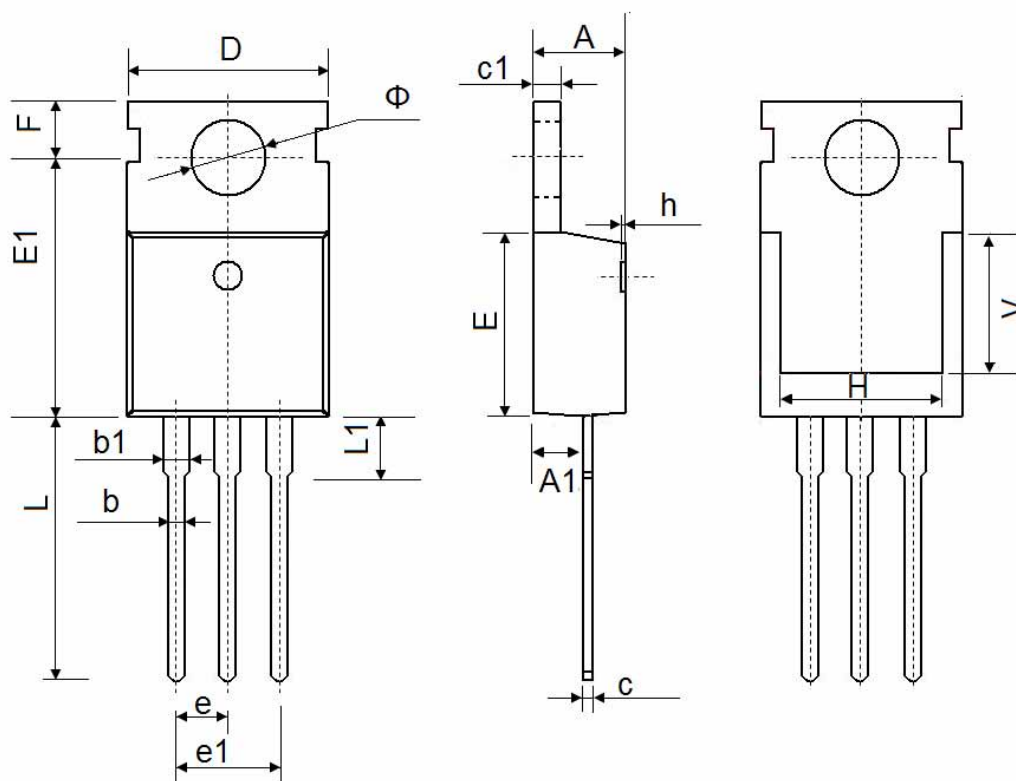


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150